



P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 30	$0.048 \text{ at V}_{GS} = -10 \text{ V}$	- 5.3		
	0.079 at V _{GS} = - 4.5 V	- 4.1		

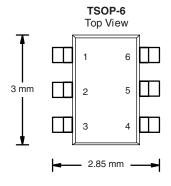
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



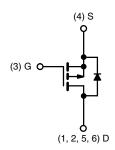
APPLICATIONS

· Load Switch



Ordering Information: Si3481DV-T1-E3 (Lead (Pb)-free)

Si3481DV-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 150 °C\d	T _A = 25 °C	I _D	- 5.3	- 4.0		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 4.2	- 3.2	^	
Pulsed Drain Current		I _{DM}	- 20		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.95		
Mariana Barra Brasilia da	T _A = 25 °C	- P _D	2.0	1.14	W	
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.73		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian and Luncking to Ambienti	t ≤ 5 s	R _{thJA}	55	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	30	36	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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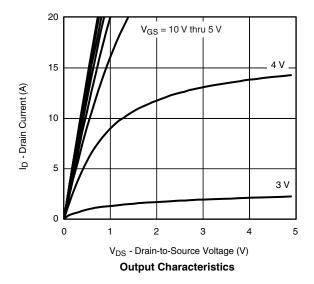
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.0		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaga Brain Current	lana	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 85 °C			- 5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			Α	
	В	V _{GS} = - 10 V, I _D = - 5.3 A		0.038	0.048	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2 A		0.063	0.079	22	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 5.3 A		12		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.85	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			15.5	25		
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5.3 \text{ A}$		2.5		nC	
Gate-Drain Charge	Q _{gd}			4.3		1	
Turn-On Delay Time	t _{d(on)}			11	17		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	22		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω		60	90	ns	
Fall Time	t _f			35	55		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dI/dt = 100 A/μs		30	60		

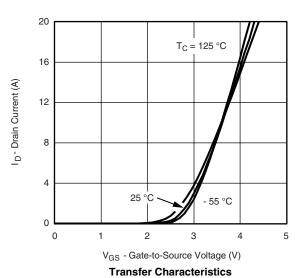
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



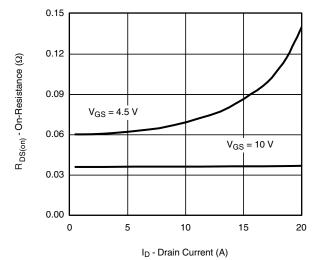




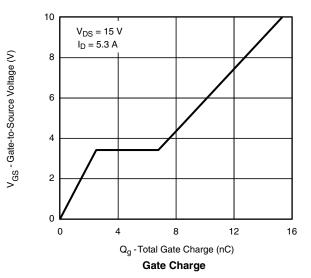


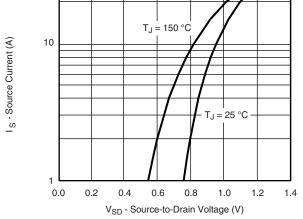


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

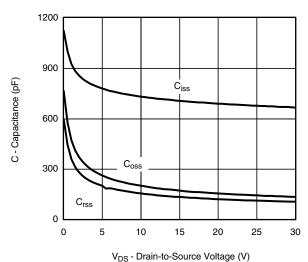


On-Resistance vs. Drain Current



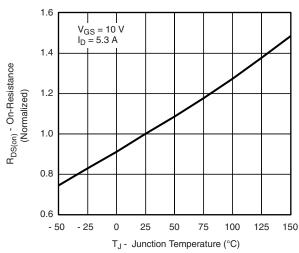


Source-Drain Diode Forward Voltage

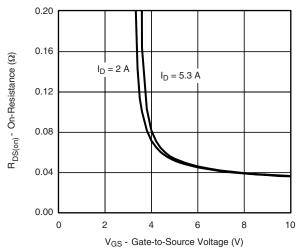


Consistence





On-Resistance vs. Junction Temperature



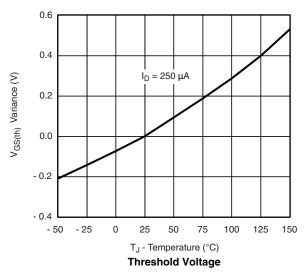
On-Resistance vs. Gate-to-Source Voltage

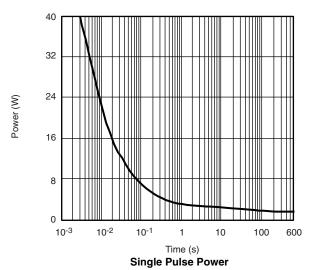
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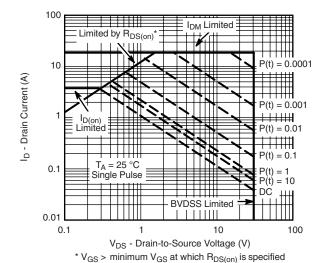
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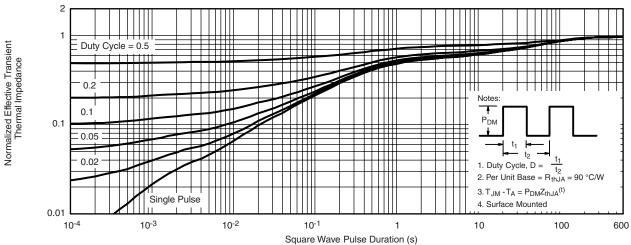
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





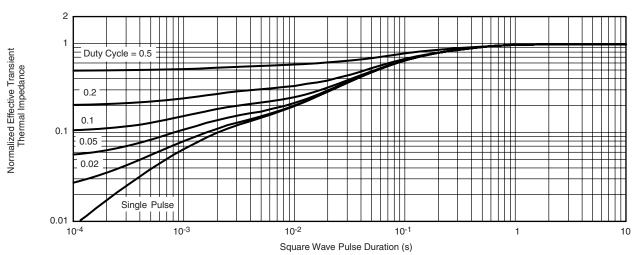


Safe Operating Area





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72105.



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